FIG. I

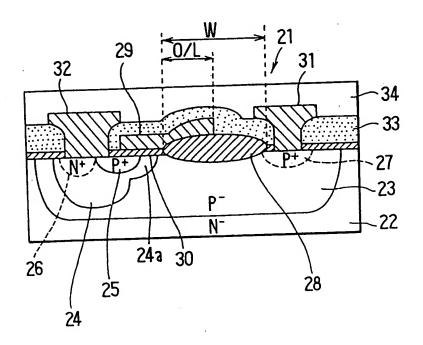
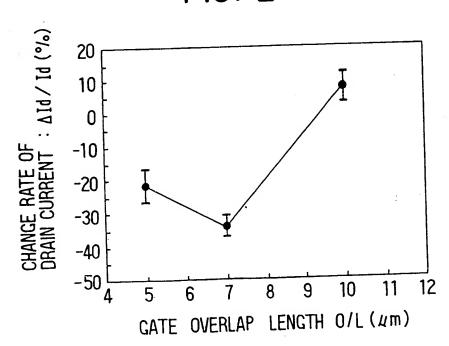
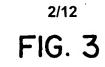
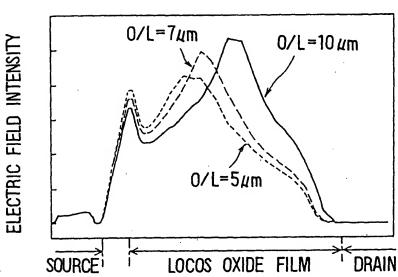
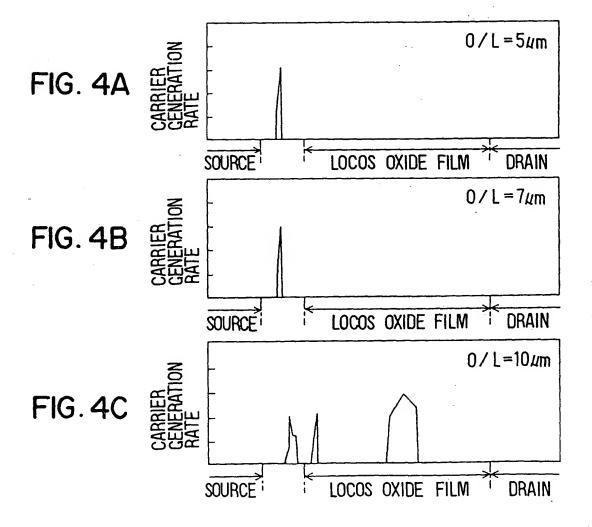


FIG. 2



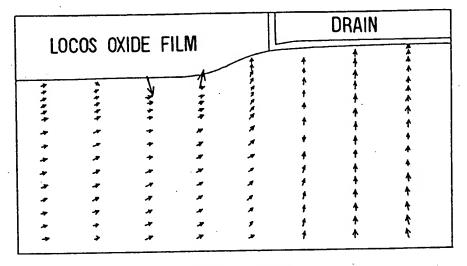






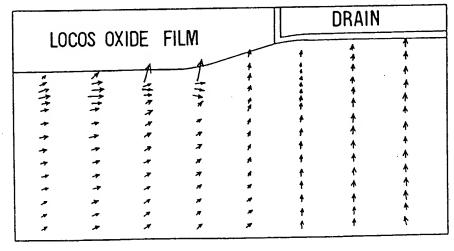
3/12

FIG. 5A



 $0/L = 10 \mu m$ 

FIG. 5B



 $0/L = 7\mu m$ 

4/12



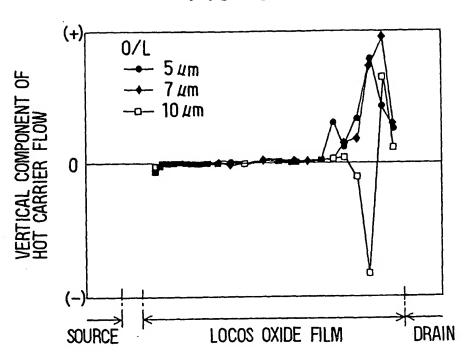
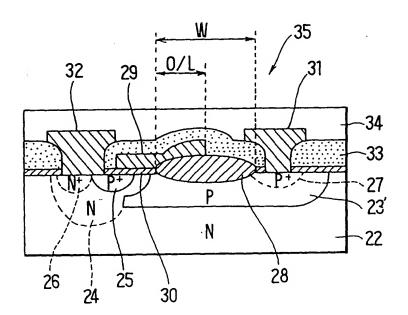


FIG. 7



5/12

FIG. 8

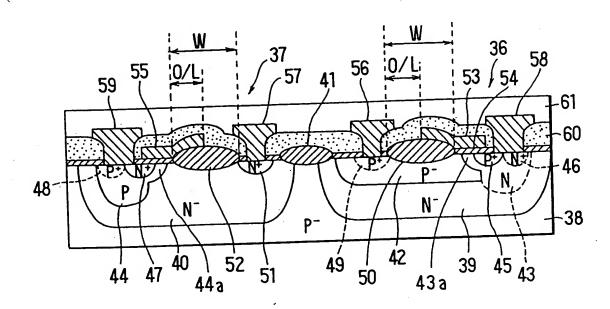
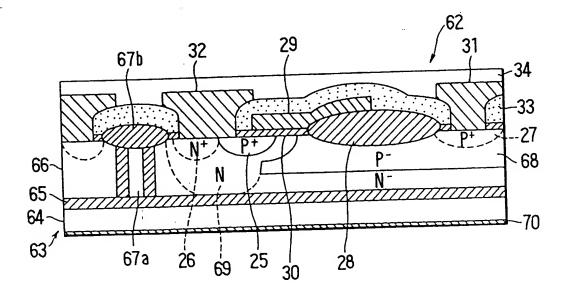


FIG. 9



Title: Semiconductor Device And Method Of Manufacturing The Same Serial No. **To be assigned** - Filed **H rewith** - Inventor(s): Hiroyasu Ito et al. Atty. Ref.: 4041J-000437/DVA

6/12

FIG. 10

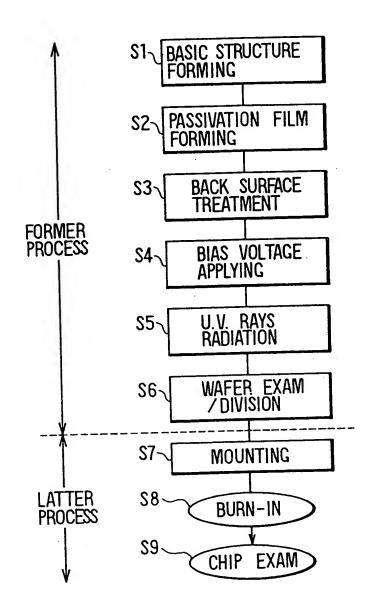


FIG. IIA

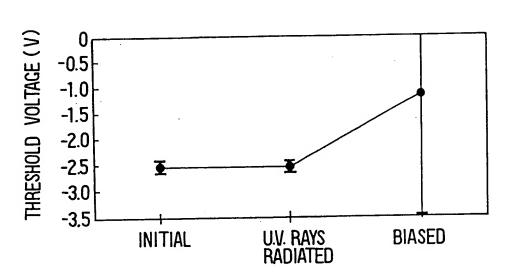


FIG. I IB

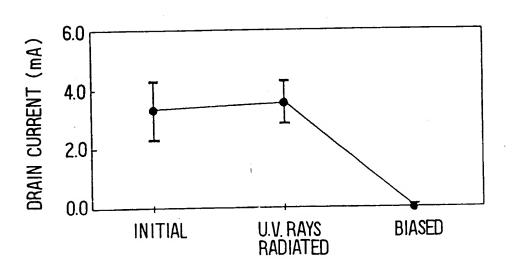


FIG. 12A

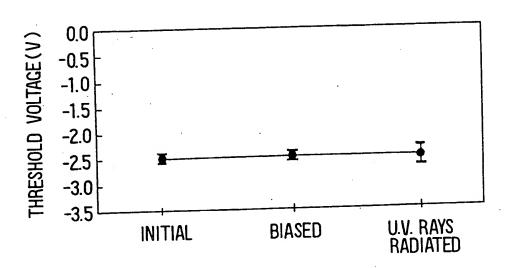
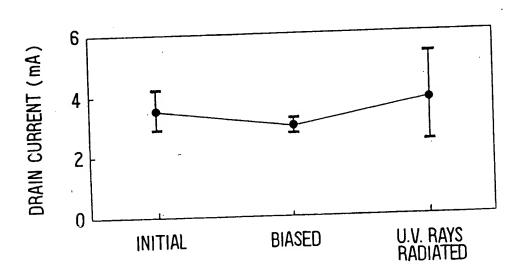


FIG. 12B



9/12

FIG. 13A

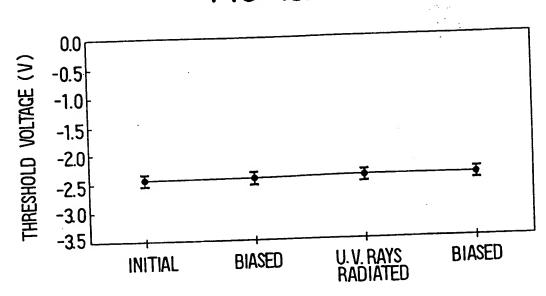
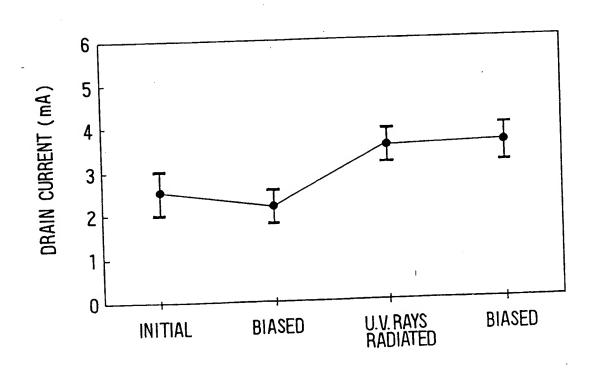
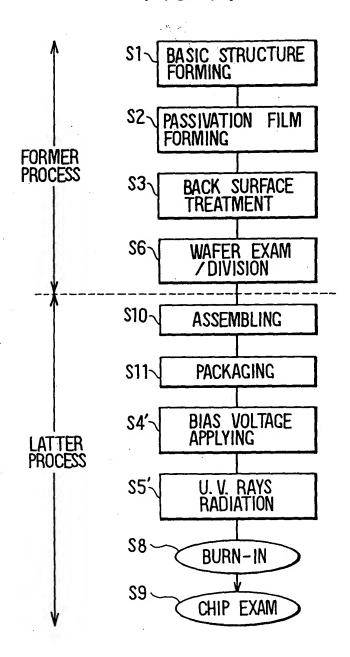


FIG. 13B



10/12

FIG. 14



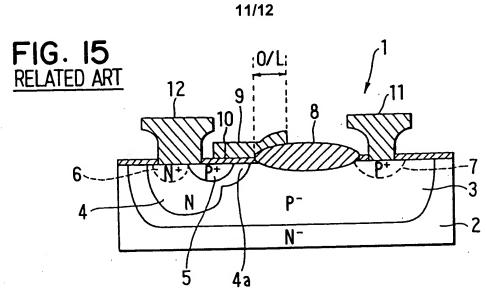
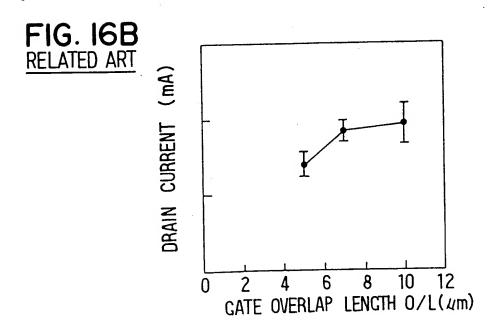


FIG. 16A
RELATED ART

ON WILLSHAM

O 2 4 6 8 10 12
CATE OVERLAP LENGTH O/L(µm)



12/12



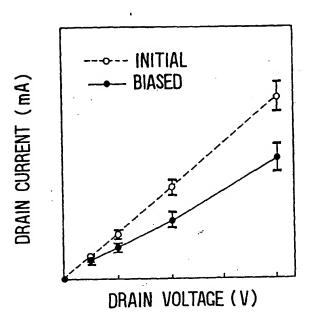


FIG. 17B RELATED ART

